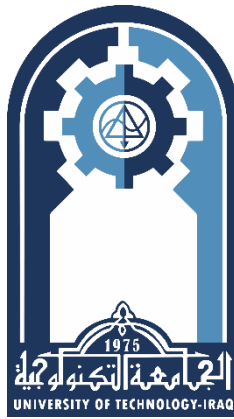


# Sputtering Process and its Types



1

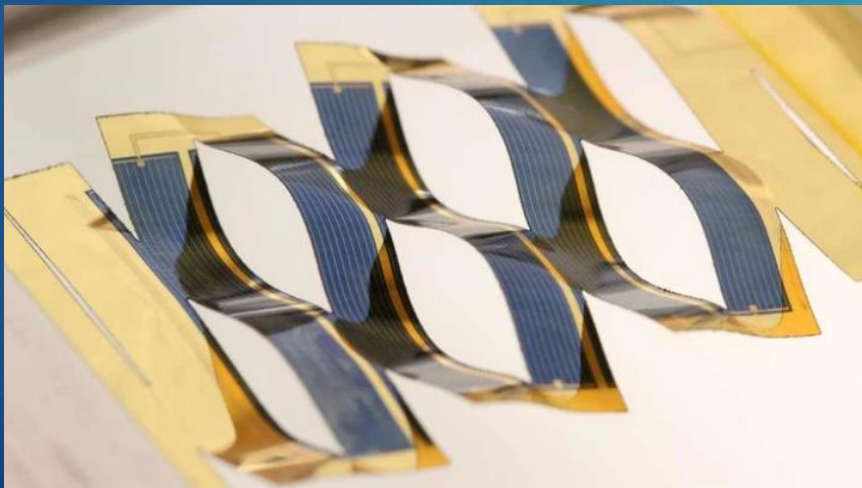
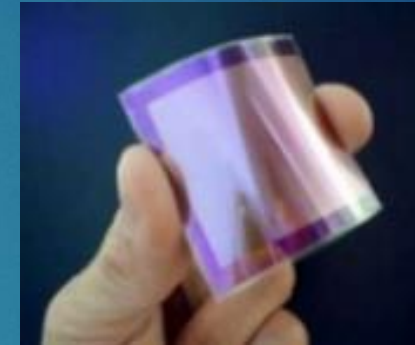
- Dr. Marwan Arbilei
- UOT – BME
- 4<sup>th</sup> Level Biomedical Instrument

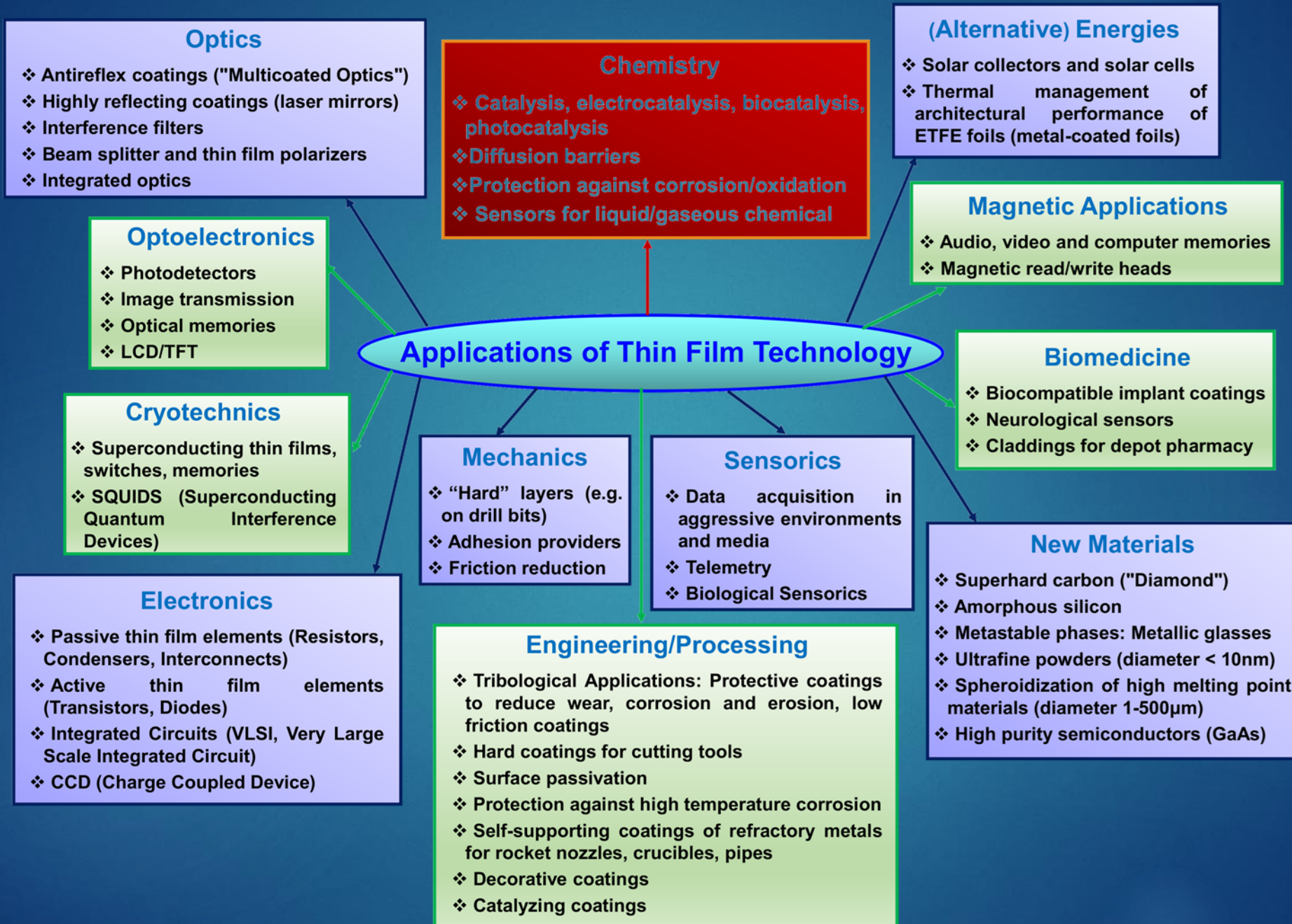


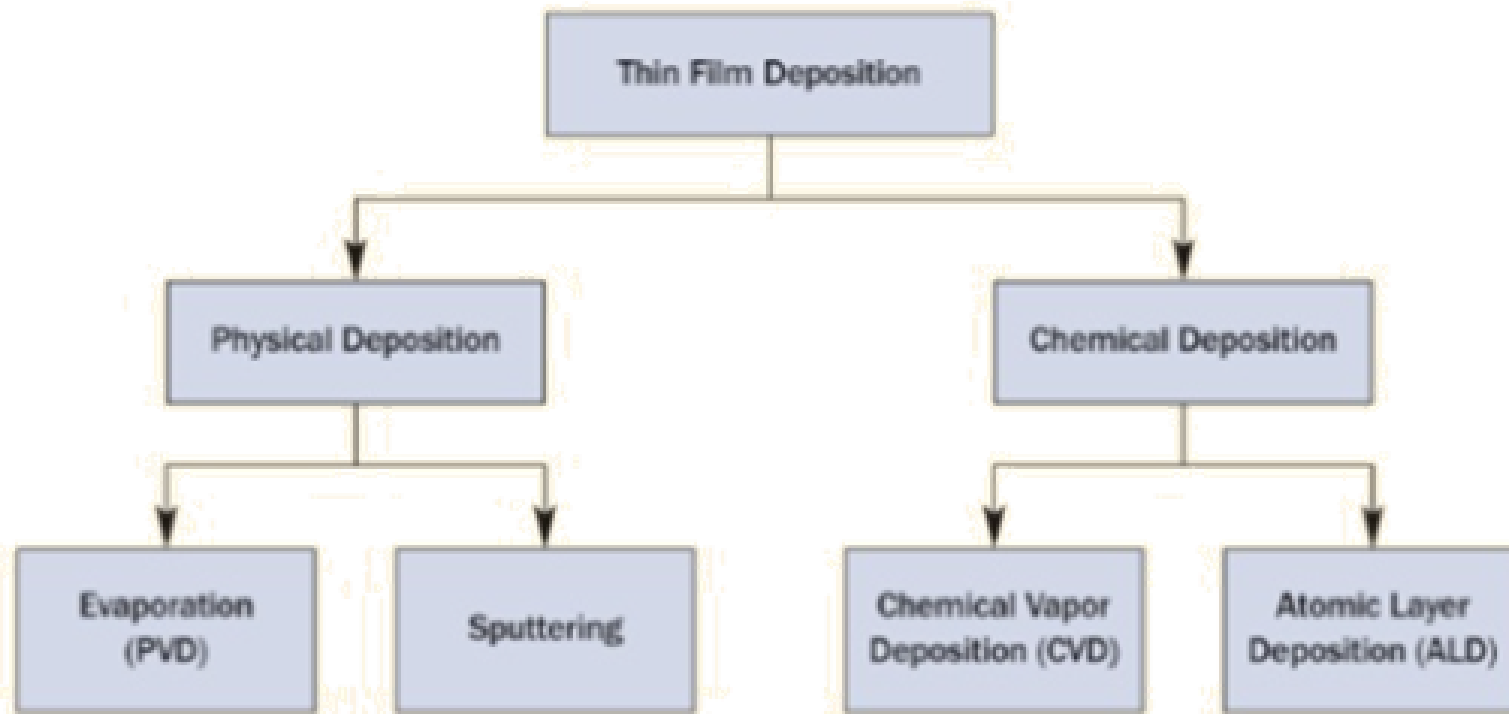
# Thin films

2

- ▶ Thin films are thin material layer ranging from fractions of a nanometer (monolayer) To several micrometers in thickness







# Synthesis of thin film



# Sputtering process

Sputtering is a term used to describe the mechanism in which atom are ejected from the surface of the material when that surface is struck by sufficient energetic particles

First discovered in 1852, and developed as thin film deposition technique by Langmuir in 1920.

Metallic film: Al-alloys, Ti, Tantalum, Nickel ,Cobalt ,Gold etc.

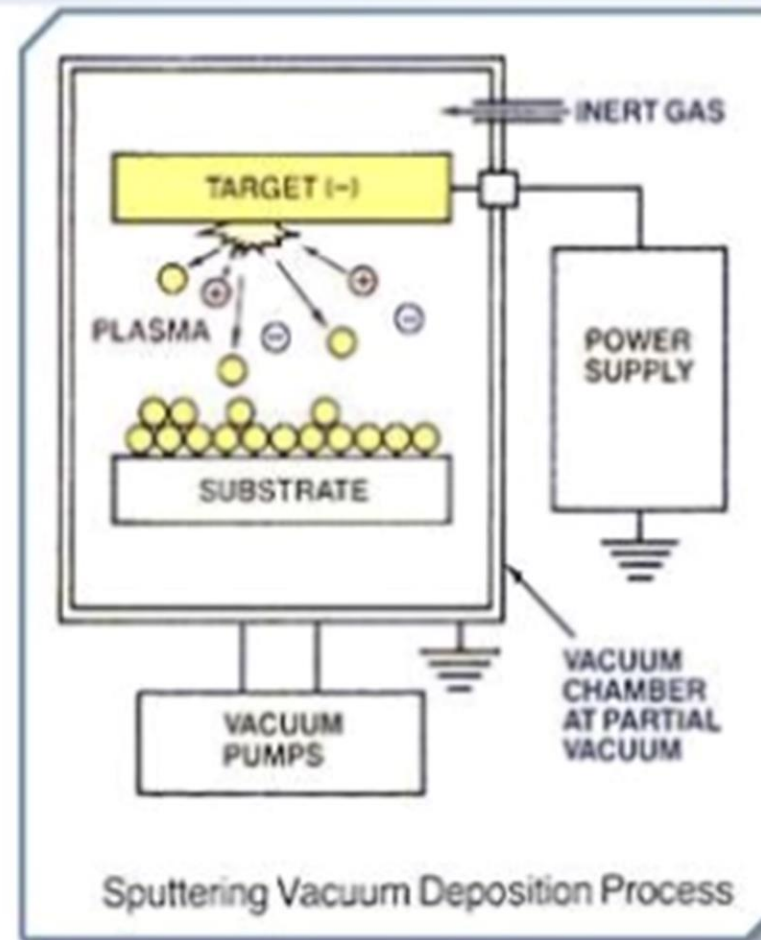
<https://www.youtube.com/watch?v=-lm0Y3Hyw-Q>



# Sputtering Explained

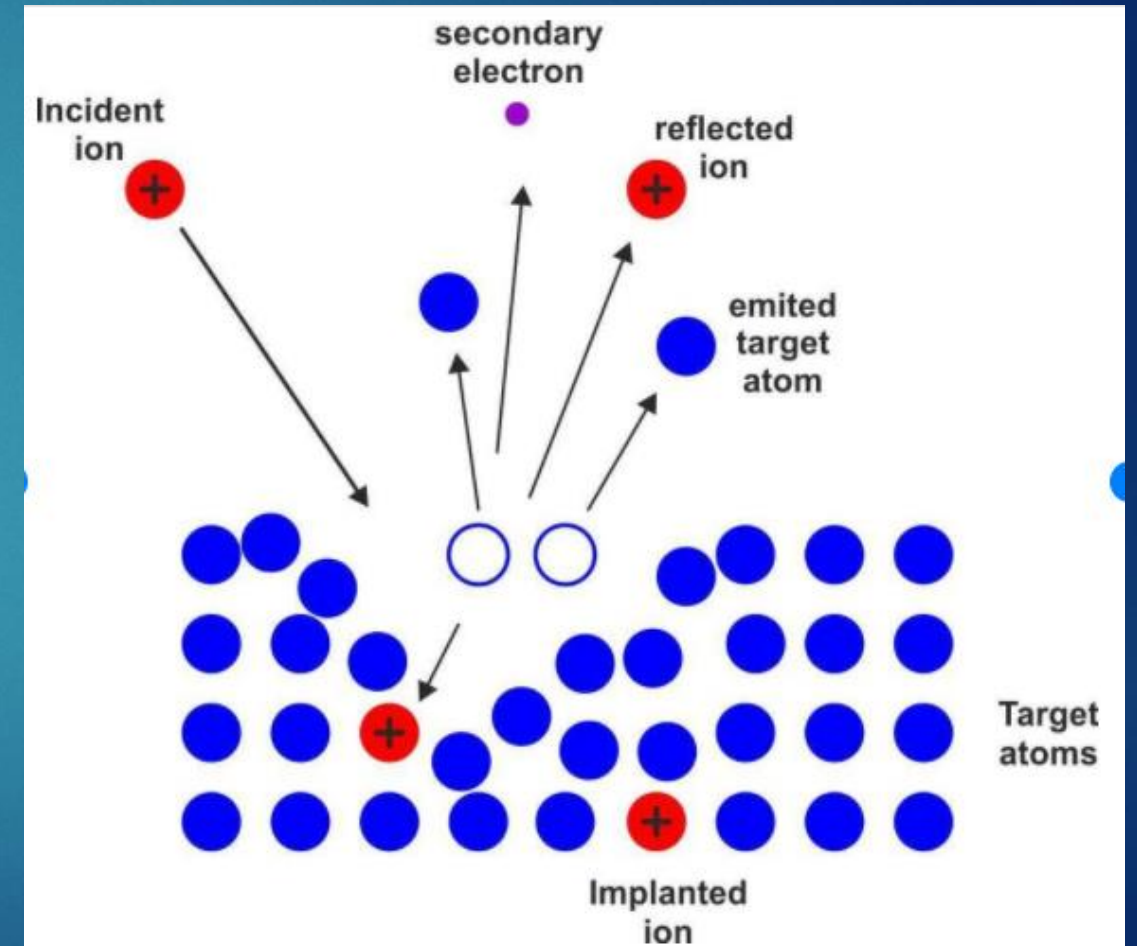
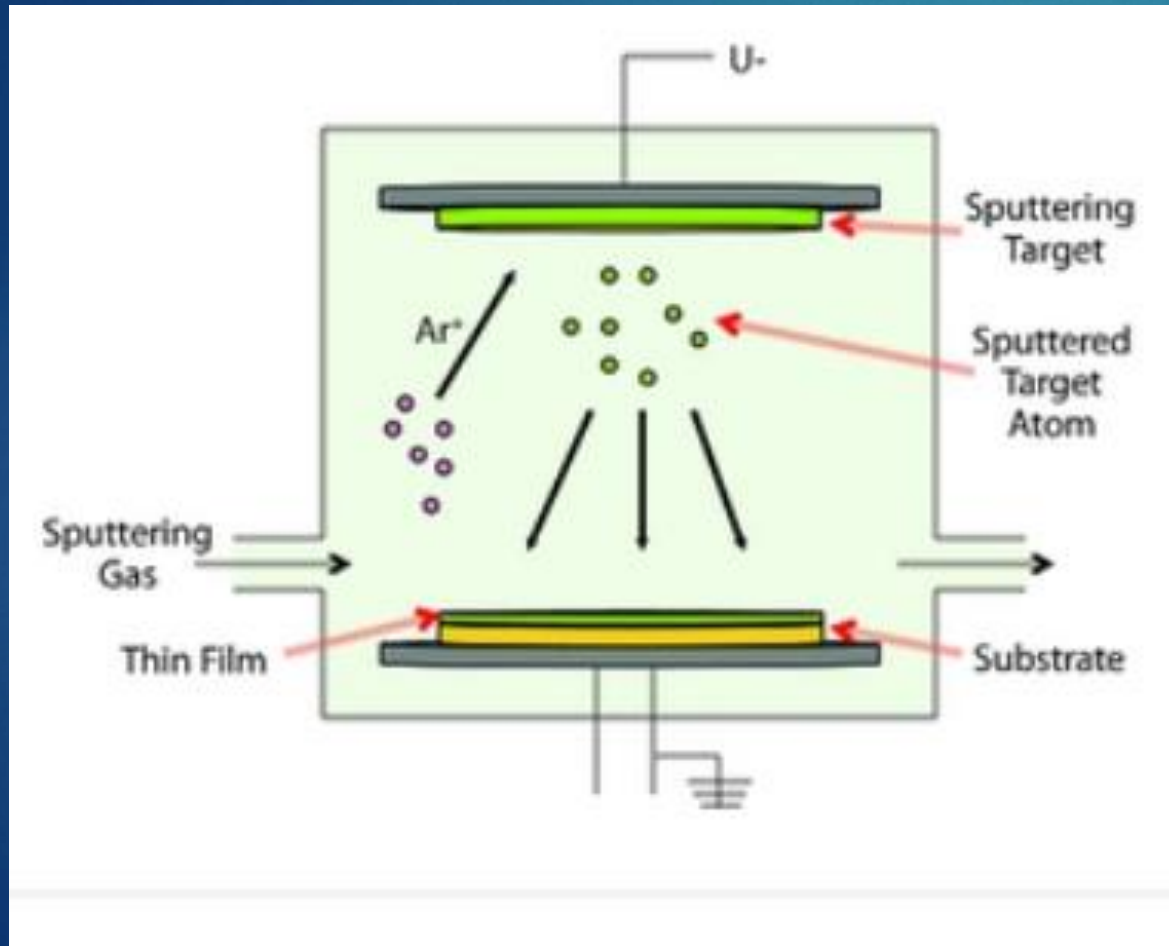
# Basic model

7



# Sputtering process

8





# Types of sputtering deposition

9

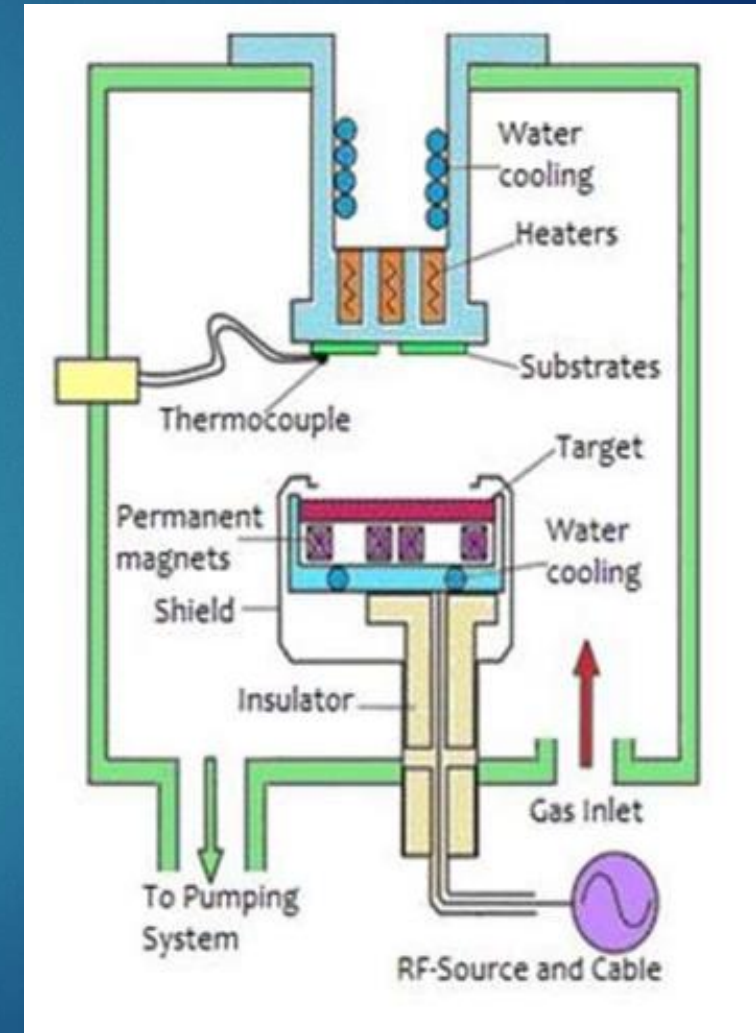
- ▶ Magnetron sputtering
- ▶ Ion-beam sputtering
- ▶ Reactive sputtering
- ▶ Ion-assisted deposition
- ▶ High target utilization sputtering (HiTUS)
- ▶ High- power impulse magnetron sputtering (HiPIMS)
- ▶ Gas flow sputtering

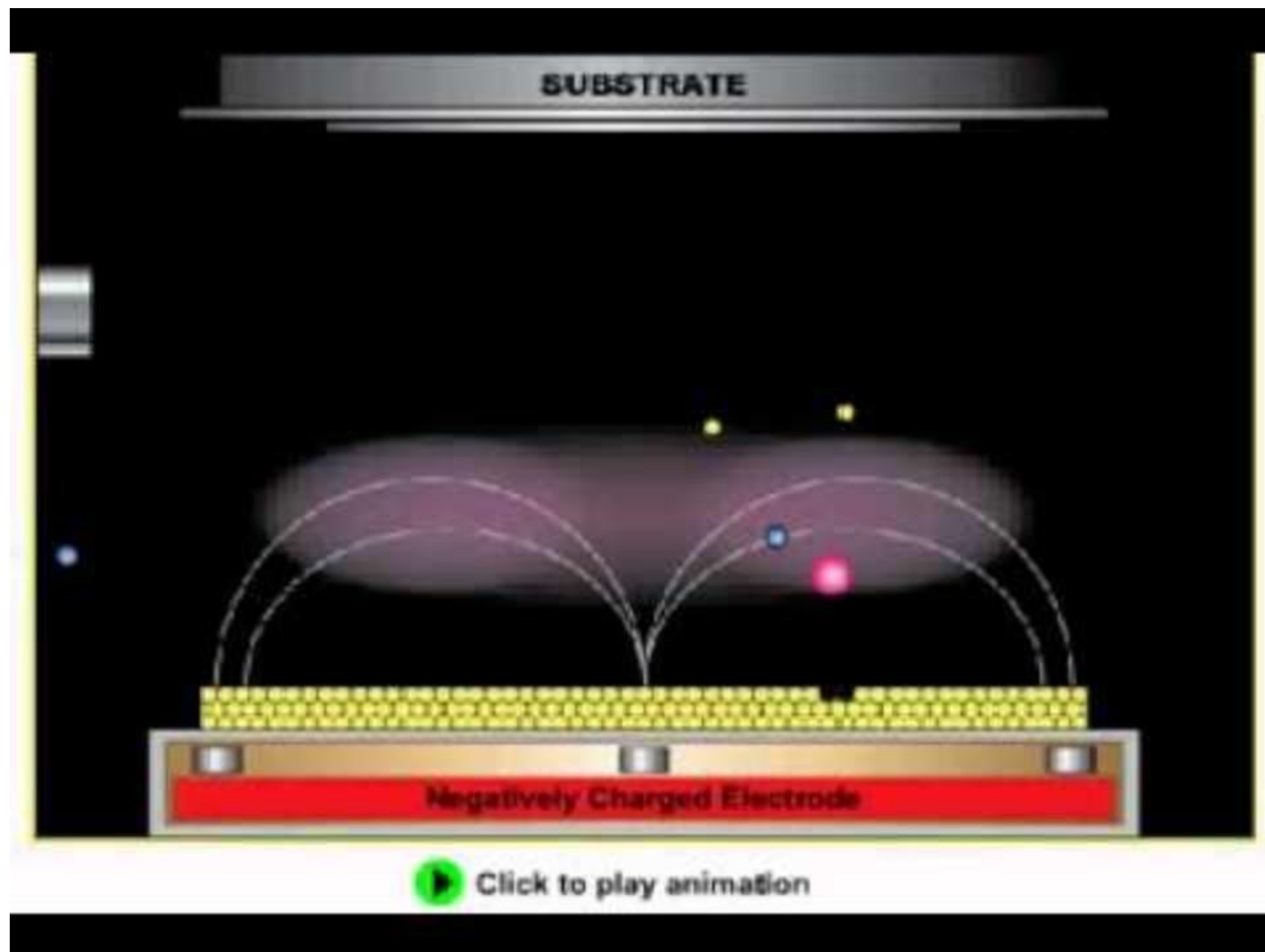
# Magnetron sputtering

<https://www.youtube.com/watch?v=Hf2kkqZhL7U>

10

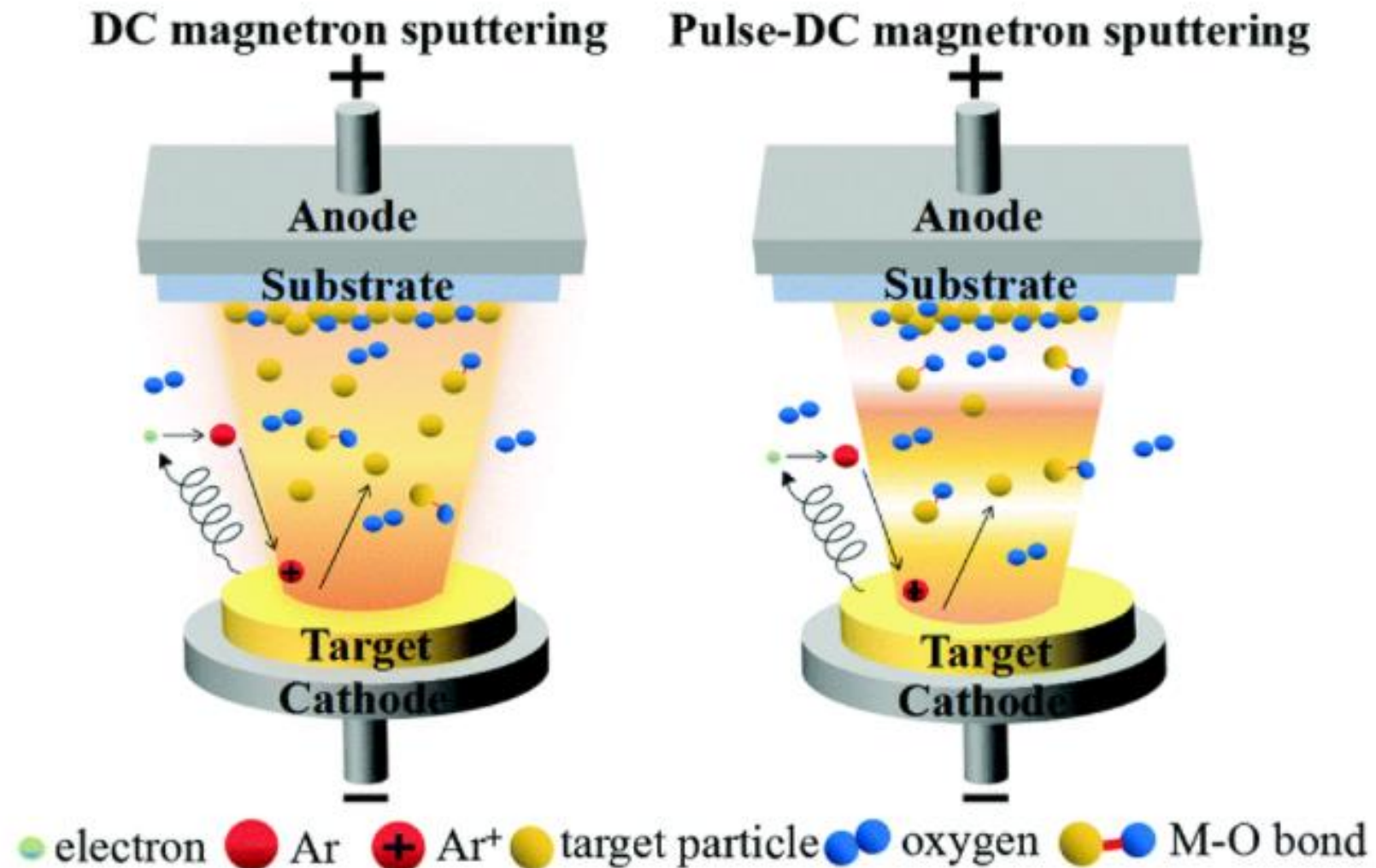
- ▶ Magnetron sputtering is the most commonly used method for a sputter deposition
- ▶ It usually utilizes a strong electric and magnetic fields to trap electrons close to the surface of the magnetron, which is known as the target.
- ▶ The electrons follow helical paths around the magnetic field lines undergoing more ionizing collisions with gaseous neutrals near the target surface than would otherwise occur
- ▶ The extra argon ions created as a result of these collisions leads to a higher deposition rate. It also means that the plasma can be sustained at a lower pressure.
- ▶ The sputtered atoms are neutrally charged and so are unaffected by the magnetic trap.





# Magnetron sputtering

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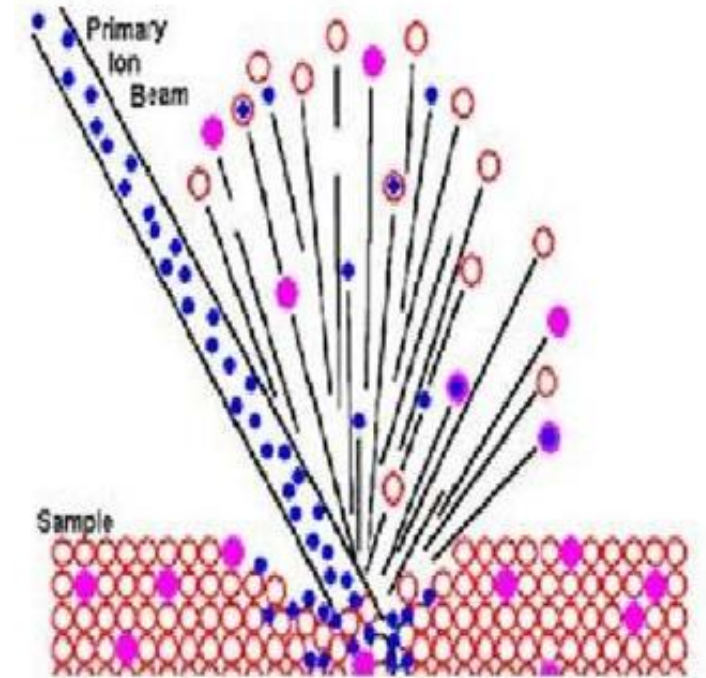




# Ion-beam sputtering

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- ▶ Ion beam sputtering utilizes an ion source to generate a relatively focused ion beam directed at the target to be sputtered.
- ▶ The ion source consists of a cathode and anode with a common central axis.
- ▶ Applying a high voltage field of 2-10 kV to the anode creates an electrostatic field inside the ion source, confining electrons around a saddle point in the center of the source.
- ▶ When argon gas is injected into the ion source, the high electric field causes the gas to ionize, creating a plasma inside the source region.
- ▶ The ions are then accelerated from the anode region to the exit aperture (cathode) creating a “collimated” ion beam.
- ▶ The resulting ion beam impinges upon a target material and, via momentum transfer between the ion and the target, sputters this material onto the sample

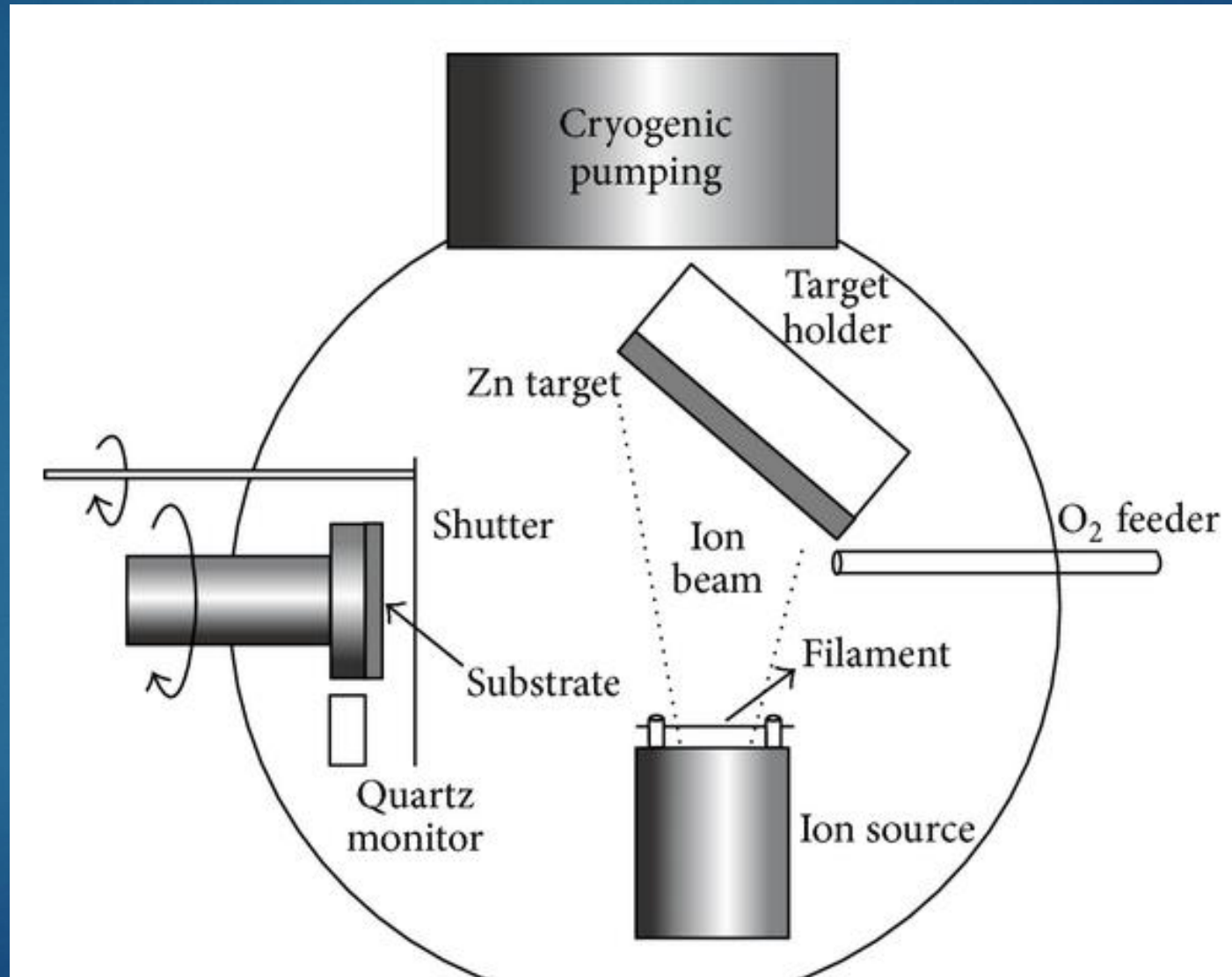




# Ion-beam sputtering

<https://www.youtube.com/watch?v=Hf2kkqZhL7U>

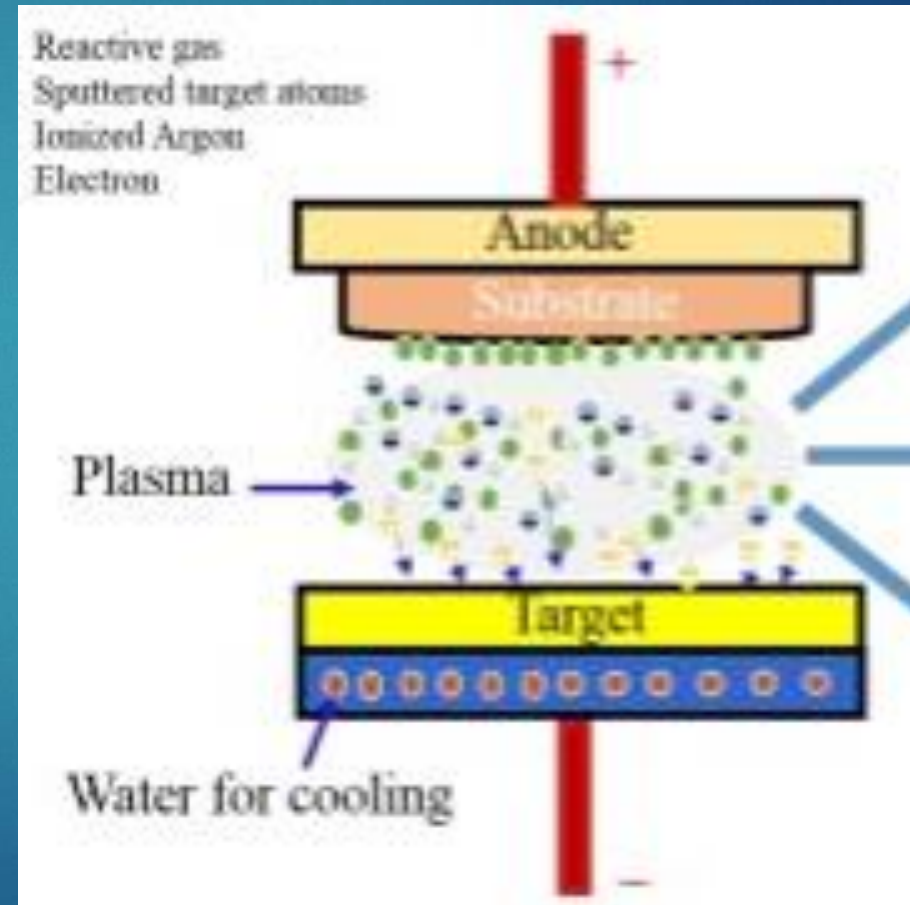
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# Reactive sputtering

15

- ▶ In reactive sputtering, the sputtered particles from a target material undergo a chemical reaction aiming to deposit a film with different composition on a certain substrate.
- ▶ The chemical reaction that the particles undergo is with a reactive gas introduced into the sputtering chamber such as oxygen or nitrogen, enabling the production of oxide and nitride films, respectively



# Application of sputtering

16

- ▶ Heads-up cockpit displays
- ▶ Jet turbine engines
- ▶ Mirrors for optical and x-ray telescopes
- ▶ Night vision equipment.
- ▶ Anti-corrosion coatings
- ▶ Anti-seize coatings
- ▶ Dies and molds
- ▶ Sewing needles
- ▶ Tool and drill bit hardening.

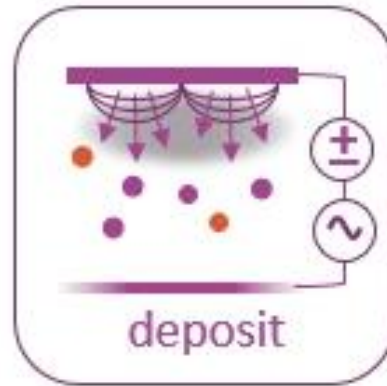
# conclusion

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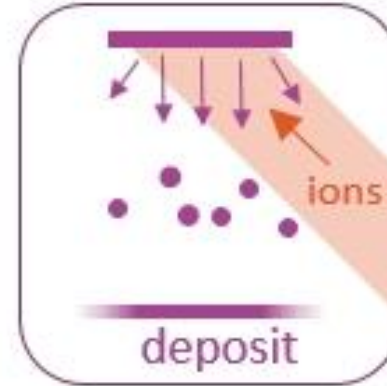
Evaporation



Magnetron sputtering



Ion Beam Deposition (IBD)



Pulsed Laser Deposition (PLD)

